

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of:

Tomoyuki ISHII et al.

Appln. No.:

Group Art Unit:

Filed: HERewith

For: SEMICONDUCTOR MEMORY DEVICE

\* \* \*

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. § 1.56, and without any  
assertion as to materiality or prior art effect, the  
documents listed on the attached Form PTO-1449 are hereby  
cited.

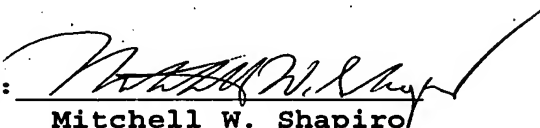
The documents on the attached List were cited in the  
specification, on pages 2-3, and their relevance is  
indicated therein.

Respectfully submitted,

MWS:lat

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By:

  
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October 15, 2003

<b>FORM PTO-1449</b>				<b>Atty. Docket No.</b> XA-9945		<b>Appln. No.</b>	
<b>LIST OF DOCUMENTS CITED BY APPLICANT</b>							
				<b>Applicant</b> Tomoyuki ISHII et al.			
				<b>Filing Date</b> HEREWITH		<b>Group</b>	
<b>U.S. PATENT DOCUMENTS</b>							
<b>Examiner Initial</b>		<b>Document Number</b>	<b>Date</b>	<b>Name</b>	<b>Class</b>	<b>Sub-class</b>	<b>Filing Date</b>
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
<b>FOREIGN PATENT DOCUMENTS</b>							
<b>Examiner Initial</b>		<b>Document Number</b>	<b>Date</b>	<b>Country</b>	<b>Class</b>	<b>Sub-class</b>	<b>Translation</b>
	AJ	2001-156275	6/08/01	Japan			Abstract
	AK						
	AL						
	AM						
	AN						
	AO						
<b>OTHER (including author, title, date, pertinent pages, etc.)</b>							
	AP	Arai, et al., "High-Density (4.4F <sup>2</sup> ) NAND Flash Technology Using Super-Shallow Channel Profile (SSCP) Engineering," IEEE International Electron Devices Meeting 2000, pp. 775-778.					
	AQ	Kobayashi, et al., "A Giga-Scale Assist-Gate (AG)-(AND)-Type Flash Memory Cell with 20-MB/s Programming Throughput for Content-Downloading Applications," IEEE International Electron Devices Meeting 2001 pp. 29-32.					
	AR	Eitan, et al., "Can NROM, a 2 Bit, Trapping Storage NVM Cell, Give a Real Challenge to Floating Gate Cells?" International Conference on Solid State Devices and Materials 1999, pp. 522-524.					
<b>Examiner</b>				<b>Date Considered</b>			
<b>XAMINER:</b> Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							